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UNITED STATES PATENT APPLICATION
FOR
PORE STRUCTURE FOR PROGRAMMABLE DEVICE

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FIELD

[0001] Programmable devices, including phase change memory devices that can be programmed by modifying the state of a phase change material.

BACKGROUND

[0002] Typical computers, or computer related devices, include physical memory, usually referred to as main memory or random access memory (RAM). Generally, RAM is memory that is available to computer programs and read-only memory (ROM) is memory that is used, for example, to store programs that boot a computer and perform diagnostics. Typical memory applications include dynamic random access memory (DRAM), static random access memory (SRAM), erasable programmable read-only memory (EPROM), and electrically erasable programmable read-only memory (EEPROM).

[0003] Solid state memory devices typically employ micro-electronic circuit elements for each memory bit (e.g., one to four transistors per bit) in memory applications. Since one or more electronic circuit elements are required for each memory bit, these devices may consume considerable chip "real estate" to store a bit of information, which limits the density of a memory chip. The primary "non-volatile" memory element of these devices, such as an EEPROM, typically employ a floating gate field effect transistor device that has limited re-programmability and which holds a charge on the gate of field effect transistor to store each memory bit. These classes of memory devices are also relatively slow to program.

[0004] Phase change memory devices use phase change materials, i.e., materials that can be electrically switched between a generally amorphous and a generally crystalline state, for electronic memory application. One type of memory element originally developed by Energy Conversion Devices, Inc. of Troy, Michigan utilizes a phase change material that can be, in one application, electrically switched between a structural state of generally amorphous and generally crystalline local order or between different detectable states of local order across the entire spectrum between completely amorphous and

completely crystalline states. Typical materials suitable for such application include those utilizing various chalcogenide elements. These electrical memory devices typically do not use field effect transistor devices as the memory storage element, but comprise, in the electrical context, a monolithic body of thin film chalcogenide material. As a result, very little chip real estate is required to store a bit of information, thereby providing for inherently high density memory chips. The state change materials are also truly non-volatile in that, when set in either a crystalline, semi-crystalline, amorphous, or semi-amorphous state representing a resistance value, that value is retained until reprogrammed as that value represents a physical state of the material (e.g., crystalline or amorphous). Thus, phase change memory materials represent a significant improvement in non-volatile memory.

[0005] One characteristic common to solid state and phase change memory devices is significant power consumption particularly in setting or reprogramming memory elements. Power consumption is significant, particularly in portable devices that rely on power cells (e.g., batteries). It would be desirable to decrease the power consumption of a memory device.

[0006] Another characteristic common to solid state and phase change memory devices is limited reprogrammable cycle life from/to an amorphous and crystalline state. Further, over time the phase change material can fail to reliably reprogram from/to an amorphous and a crystalline state. It would be desirable to increase the programmable cycle life of the phase change memory material.

BRIEF DESCRIPTION OF THE DRAWINGS

[0007] Advantages of the invention will become apparent upon reading the following detailed description and upon reference to the drawings, in which:

Fig. 1 is a schematic diagram of an embodiment of an array of memory elements;

Fig. 2 schematically illustrates a cross-sectional planar side view of a portion of a semiconductor substrate having dielectric trenches formed therein defining a

z-direction thickness of a memory cell in accordance with one embodiment of forming a memory element on a substrate;

Fig. 3 depicts the structure of **Fig. 2**, through the same cross-sectional view, after the introduction of dopants to form an isolation device for a memory element;

Fig. 4 depicts the structure of **Fig. 3** after forming trenches;

Fig. 5 depicts a schematic top view of the structure of **Fig. 4**;

Fig. 6 depicts the structure of **Fig. 4** after forming contacts;

Fig. 7 depicts the structure of **Fig. 6**, through the same cross-sectional view, after forming a masking material and a dielectric material;

Fig. 8 depicts another cross-section view of the structure of **Fig. 7**, after forming an opening through the dielectric exposing the contact;

Fig. 9 depicts the structure of **Fig. 8**, through the same cross-sectional view, after conformally forming a spacer within the opening;

Fig. 10 depicts the structure of **Fig. 9**, through the same cross-sectional view, after etching the spacer;

Fig. 11 depicts the same cross-sectional view of the structure of **Fig. 10**, after forming programmable material, a barrier and a conductor;

Fig. 12 depicts the same cross-sectional view of the structure of **Fig. 11**, after patterning the programmable material, barrier and conductor;

Fig. 13 depicts another cross-sectional view of the structure of **Fig. 12**;

Fig. 14 depicts the same cross-sectional view of the structure of **Fig. 13**, after forming a dielectric material and a signal line; and

Fig. 15 depicts one method of forming a memory device having a structure similar to that described by **Fig. 14**.

Fig. 16 depicts one system embodiment including a memory having a structure similar to that described by **Fig. 14**.

DETAILED DESCRIPTION

[0008] Exemplary embodiments are described with reference to specific configurations. Those of ordinary skill in the art will appreciate that various changes and modifications can be made while remaining within the scope of the appended claims. Additionally, well-known elements, devices,

components, circuits, process steps and the like may not be set forth in detail in order to avoid obscuring the invention.

[0009] A memory device utilizing programmable material to determine the state of memory elements of the device is described that reprograms to an amorphous and crystalline state with improved (generally lower) power consumption relative to previous devices. In an embodiment, a minimized quantity of programmable (e.g. phase change) material is utilized, and the programmable material to be set/reprogrammed is localized on a contact with generally even current distribution. In another embodiment, a method of fabricating a programmable memory device is described such that an opening is formed through a dielectric exposing a contact formed on a substrate. A spacer is formed within the opening and programmable material is subsequently formed within the opening. The spacer minimizes the programmable material on the contact and minimizes the overall quantity of programmable material utilized by the memory device.

[0010] The described memory device and method provides improved device reliability, improved programmable cycle life, and lower cost and scalability relative to previous devices. Further, in an embodiment, the apparatus is manufacturable with conventional process toolsets and facilities.

[0011] **Fig. 1** shows a schematic diagram of an embodiment of a memory array comprised of a plurality of memory elements presented and formed in the context of the description provided herein. In this example, the circuit of memory array 5 includes an xy grid with memory elements 30 electrically interconnected in series with isolation devices 25 on a portion of a chip. Address lines 10 (e.g., columns) and 20 (e.g., rows) are connected, in one embodiment, to external addressing circuitry in a conventional manner. One purpose of the xy grid array of memory elements in combination with isolation devices is to enable each discrete memory element to be read and written without interfering with the information stored in adjacent or remote memory elements of the array.

[0014] **Fig. 2** also depicts shallow trench isolation (STI) structures 130 formed in epitaxial portion 120 of substrate 100. As will become apparent in the subsequent discussion, STI structures 130 serve, in one aspect, to define the z-direction thickness of a memory cell, with at this point only the z-direction thickness of a memory cell defined. In one embodiment, memory cell z-direction regions 135A and 135B are patterned as strips with the x-direction dimension greater than the z-direction dimension. In another aspect, STI structures 130 serve to isolate individual memory elements from one another as well as associated circuit elements (e.g., transistor devices) formed in and on the substrate. Current state of the art photolithography techniques utilized to pattern STI structures define the z-direction thickness of memory cell regions

135A and 135B can produce feature sizes (z-direction thickness) as small as 0.25 microns (μm).

[0015] **Fig. 3** depicts the structure of **Fig. 2** after further fabrication operations in memory cell regions 135A and 135B. Within each memory cell region (strip), overlying epitaxial portion 120 of substrate 100 is first conductor or signal line material 140. In one example, first conductor or signal line material 140 is N-type doped polysilicon formed by the introduction of, for example, phosphorous or arsenic to a concentration on the order of about 10^{18} to 10^{19} atoms/cm³ (e.g., N⁺ silicon). In this example, first conductor or signal line material 140 serves as an address line, a row line (e.g., row line 20 of **Fig. 1**). Overlying first conductor or signal line material 140 is an isolation device (e.g., isolation device 25 of **Fig. 1**). In one example, the isolation device is a PN diode formed of N-type silicon portion 150 (e.g., dopant concentration on the order of about 10^{14} to 10^{18} atoms/cm³) and P-type silicon portion 160 (e.g., dopant concentration on the order of about 10^{19} to 10^{20} atoms/cm³). Although a PN diode is shown, it is to be appreciated that other isolation structures are similarly suitable. Such devices include, but are not limited to, metal oxide semiconductor (MOS) devices.

[0016] **Fig. 4** depicts the structure of **Fig. 3** from an xy perspective after forming trenches 190 in epitaxial portion 120 of substrate 100. Trenches 190 are formed, in this example, orthogonal to STI structures 130. Trenches 190 define the x-direction thickness of a memory cell. According to current photolithographic techniques, a suitable feature size for the x-direction thickness is as small as 0.25 μm . **Fig. 4** also depicts memory cells 145A and 145B separated by trenches 190, having a z-direction thickness defined by STI structures 130 and an x-direction thickness defined by trenches 190. The definition of the x-direction thickness involves, in one embodiment, an etch to the conductor or signal line 140 of the memory line stack to define memory cells 145A and 145B of memory cell region 135A. In the case of an etch, the etch proceeds through the memory line stack to, in this example, a portion of conductor or signal line 140. A timed etch can be utilized to stop an etch at this

point. Following the patterning, N-type dopant is introduced at the base of each trench 190 to form pockets 200 having a dopant concentration on the order of about 10^{18} to 10^{20} atoms/cm³ (e.g., N⁺ region) between memory cells 145A and 145B.

[0017] Following the introduction of pockets 200, a dielectric material such as silicon dioxide is introduced in trenches 190 to form STI structures 132. The superior surface (as viewed) may then be planarized with, for example, a chemical-mechanical polish. **Fig. 5** depicts an xz perspective of the structure of **Fig. 4** with memory cells (e.g., memory cells 145A and 145B) separated by STI structures 130 and 132.

[0018] **Fig. 6** depicts the structure of **Fig. 4** (i.e., an xy perspective) following the formation of a material of, in this example, refractory metal silicide such as cobalt silicide (CoSi₂) in a portion of p-type silicon portion 160 to define contact 170. Contact 170, in one aspect, serves as a low resistance material in the fabrication of peripheral circuitry (e.g., addressing circuitry) of the circuit structure on the chip.

[0019] **Fig. 7** depicts the structure of **Fig. 6** after the introduction of masking material 180. As will become more clear later, masking material 180 serves, in one sense, as an etch stop for a subsequent etch operation. In one embodiment, a suitable material for masking material 180 is a dielectric material such as silicon nitride (Si₃N₄).

[0020] **Fig. 7** also depicts dielectric material 210 introduced over the structure to a thickness on the order of 100Å to 50,000Å sufficient to blanket memory cells 145A and 145B. In one embodiment, dielectric material 210 is SiO₂. In another embodiment, dielectric material 210 is a material selected for its reduced thermal conductivity, κ , preferably a thermal conductivity less than κ_{SiO_2} , more preferably three to 10 times less κ_{SiO_2} . As a general convention, SiO₂ and Si₃N₄ have κ values on the order of 1.0. Thus, in addition to SiO₂, suitable materials for dielectric material 210 include those materials that have κ values less than 1.0. Certain high temperature polymers having κ values less

than 1.0, include carbide materials, Aerogel, Xerogel (κ on the order of 0.1) and their derivatives.

[0021] **Fig. 8** depicts the structure of **Fig. 7**, through the same cross-sectional view, after forming openings 220 through dielectric 210 and masking material 180, exposing contact 170. In one embodiment, openings 220 are formed by patterning of circular holes etched through dielectric 210 and masking material 180, using conventional photolithography and dry etching techniques. In terms of state of the art photolithography techniques, circular openings as small as 0.25 μm in diameter can be patterned. It is to be appreciated that, in addition to circular openings, other openings such as rectangular openings could alternatively be employed.

[0022] **Fig. 9** depicts the structure of **Fig. 8**, through the same cross-sectional view, after forming spacer material 402 within openings 220 and on dielectric 210. In one embodiment, spacer material 402 is conformally formed, for example by chemical vapor deposition of tetra-ethyl-ortho-silicate (TEOS) on the substrate. At this point of fabrication, spacer material covers contact 170 within openings 220.

[0023] **Fig. 10** depicts the structure of **Fig. 9** after spacer material 402 is etched to form dielectric spacers (spacer material portions 402A) inside openings 220. In one embodiment, spacer material 402 is anisotropically etched using a timed etch. In one aspect, that will become more clear later, spacer material 402 serves to reduce the quantity of programmable material 404 (**Fig. 11**) on contact 170.

[0024] **Fig. 11** depicts the structure of **Fig. 10** after introducing programmable material 404 within openings 220, on contact 170 and on dielectric 210. In one embodiment, programmable material 404, a phase change material that has a property such that a physical state (e.g., crystalline, amorphous) can be modified with the application of an amount of energy (e.g., electrical energy, thermal energy). Chalcogenide materials having the general formula are known to be suitable for this purpose such that chalcogenide

materials can be introduced on the substrate and on contact 170 by conventional deposition techniques.

[0025] As further illustrated in **Fig. 11**, following the introduction of programmable material 404, barrier material 408 is formed on programmable material 404 and conductor 410 is formed on barrier material 408, in accordance with an embodiment. Barrier material 408 serves, in an aspect, to prevent any chemical reaction between programmable material 404 and conductor 410. In an embodiment, programmable material 404, spacer 402, barrier material 408 and conductor 410 are formed using conventional patterning techniques. In an embodiment, barrier material 408 includes at least one of titanium and titanium nitride. Titanium and/or Titanium nitride coatings can be deposited uniformly on a substrate, showing good adhesion in that they resist flaking, blistering, chipping and peeling. In an embodiment, programmable material 404 includes a phase change material of a chalcogenide alloy and contact 170 includes CoSi_2 . In an embodiment, chalcogenide alloys suitable as programmable material 404 include at least one element from column VI of the Periodic Table Of The Elements. In an embodiment, $\text{Ge}_2\text{Sb}_2\text{Te}_5$ is utilized as programmable material 404. Other chalcogenide alloys utilized as programmable material 404 include GaSb , InSb , InSe , Sb_2Te_3 , GeTe , InSbTe , GaSeTe , SnSb_2Te_4 , InSbGe , AgInSbTe , $(\text{GeSn})\text{SbTe}$, $\text{GeSb}(\text{SeTe})$, and $\text{Te}_{81}\text{Ge}_{15}\text{Sb}_2\text{S}_2$.

[0026] In the structure illustrated in **Fig. 11**, the contact area of programmable material 404 and contact 170 is minimized by the presence of spacer material portions 402A. In an aspect, the dimensions of openings 220 expose a first contact area of contact 170. In an aspect, a second contact area, less than the first contact area, is exposed by spacer material 402 and/or spacer material portions 402A. By minimizing the quantity of programmable material 404, the quantity of programmable material 404 that undergoes, for example, a phase change from/to amorphous and crystalline on contact 170 (as shown by region 406) is localized. Region 406, shown between spacer material portions 402A, defines a limited and localized programming region of

programmable material 404, adding to the programmable reliability from and to an amorphous and crystalline state of programmable material 404. In general, by localizing the phase change area, less current is required through programmable material 404 during programming and reading, and less power consumption results.

[0027] In an aspect, current passes, in general, from conductor 410 through programmable material 404 to contact 170 with even distribution, minimizing current non-uniformity, and avoiding hot spots throughout programmable material 404 and contact 170. Further, because less current is utilized through programmable material 404, the resistivity of contact 170 can be minimized, thereby providing flexibility in regards to choice of material selected for contact 170.

[0028] **Fig. 12** depicts the structure of **Fig. 11**, from an xy perspective, after forming openings 412. Openings 416 serve, in one aspect, to define the x-direction thickness of programmable material 404, barrier material 408 and conductor 410. Openings 416 serve, in another aspect, to isolate individual memory elements from one another as well as associated circuit elements (e.g., transistor devices) formed on the substrate. In one embodiment, openings 416 are formed by patterning of openings through conductor 410, barrier material 408 and programmable material 404. The patterning can be accomplished using conventional photolithographic and etch techniques. In this example, the etching proceeds through conductor 410, barrier material 408 and programmable material 404, to the exclusion of dielectric 210. According to current photolithographic techniques, a suitable feature size for the x-direction thickness of openings 416 include as small as 0.25 μm .

[0029] **Fig. 13** depicts another cross-sectional view, from the yz perspective, of the structure of **Fig. 12**. A heat sink, as illustrated by an area generally defined by lines 500 maintains a more stable temperature and cooler interface between programmable material 404 and contact 170.

[0030] **Fig. 14** shows the structure of Figure 13 after forming dielectric material 412 over conductor 410. Dielectric material 412 is, for example, SiO₂ or other suitable material that is formed on conductor 410 to electronically isolate conductor 410. Following the formation, dielectric material 412 is planarized and a via is formed in a portion of the structure through dielectric material 412, dielectric material 210, and dielectric material 180 to contact 170. The via is filled with conductive material such as tungsten (W) and a barrier material such as a combination of titanium (Ti) and titanium nitride (TiN). Techniques for introducing dielectric material 412, forming and filling conductive vias, and planarizing are known to those skilled in the art. The structure shown in **Fig. 14** also shows additional conductor or signal line material 414 formed and patterned to mirror that of conductor or signal line material 140 (e.g., row line) formed on substrate 100. Mirror conductor line material 414 mirrors conductor or signal line material 140 and is coupled to conductor or signal line material 140 through the conductive via. By mirroring a doped semiconductor such as N-type silicon, mirror conductor line material 414 serves, in one aspect, to reduce the resistance of conductor or signal line material 140 in a memory array, such as memory array 5 illustrated in **Fig. 1**. A suitable material for mirror conductor line material 414 includes an aluminum material, such as an aluminum alloy.

[0031] **Fig. 15** describes a method in forming a programmable memory device in accordance with an embodiment.

[0032] Further, as depicted in **Fig. 16**, a memory array such as memory device 5 (**Fig. 1**) wherein the individual memory cells have a structure similar to that described with reference to **Fig. 14** and the accompanying text can be incorporated into a suitable system. In one embodiment, system 700 includes microprocessor (CPU) 704, input/output (I/O) port 706, and memory 702. Microprocessor 704, I/O port 706, and memory 702 are connected by data bus 712, address bus 716 and control bus 714. Microprocessor 704 fetches instructions or reads data from memory 702 by sending out an address on address bus 716 and a memory read signal on control bus 714. Memory 702

outputs the addressed instruction or data word to microprocessor 704 on data bus 712. Microprocessor 704 writes a data word to memory 702 by sending out an address on address bus 716, sending out the data word on data bus 712, and sending a memory write signal to memory 702 on control bus 714. I/O port 706 is utilized to couple to at least one of input device 708 and output device 710. An individual memory cell in memory 702 such as memory device 5 (**Fig. 1**) includes a contact on a substrate, a dielectric on the contact having an opening exposing the contact, a programmable (e.g. phase change) material formed within the opening and on the contact, and a conductor in contact with the, e.g., programmable material. The programmable material is either read or written depending on the operation. In a read operation, the phase of phase change material is determined by whether or not current can pass between the conductor and the contact. If current can pass, the data signal can be configured a "1". If a current cannot pass, the data can be configured a "0".

[0033] Having disclosed exemplary embodiments, modifications and variations may be made to the disclosed embodiments while remaining within the spirit and scope of the invention as defined by the appended claims.